Abstracts

Cryogenically Cooled GaAs FET Amplifier with a 1.1-dB Noise Figure at 5.0 GHz

J. Pierro. "Cryogenically Cooled GaAs FET Amplifier with a 1.1-dB Noise Figure at 5.0 GHz." 1976 MTT-S International Microwave Symposium Digest of Technical Papers 76.1 (1976 [MWSYM]): 93-96.

A 4.5 to 5.0 GHz gallium arsenide field-effect transistor (GaAs FET) amplifier cryogenically cooled to 20 K is described. A noise figure of 1.1 dB maximum is achieved over the band. Gain per stage is approximately 10 dB. A noise analysis is performed to predict noise figure dependence on the physical temperature of the amplifier.

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